

FEATURES

Complimentary to SS8050

Marking : Y2

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-1500	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

SS8550 (PNP)


ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=-100\mu A, I_E=0$	-40		V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=-0.1mA, I_B=0$	-25		V
Emitter-base breakdown voltage	V_{EBO}	$I_E=-100\mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-20V, I_B=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	120	400	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-800mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-800mA, I_B=-80mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-800mA, I_B=-80mA$		-1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=-1V, I_C=-10mA$		-1	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA$ $f=30MHz$	100		MHz
output capacitance	C_{ob}	$(V_{CB}=-10V, I_E=0, f=1MHz)$		20	pF

 CLASSIFICATION OF h_{FE}

Rank	L	H	J
Range	120-200	200-350	300-400

SS8550 Typical Characteristics

